imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





LIS3L02AS5

MEMS INERTIAL SENSOR: 3-axis - ±2g/6g LINEAR ACCELEROMETER

Features

- 4.5 TO 5.5V SINGLE SUPPLY OPERATION
- LOW POWER CONSUMPTION
- ±2g/±6g USER SELECTABLE FULL-SCALE
- 0.5mg RESOLUTION OVER 100Hz BANDWIDTH
- EMBEDDED SELF TEST AND POWER DOWN
- OUTPUT VOLTAGE, OFFSET AND SENSITIVITY RATIOMETRIC TO THE SUPPLY VOLTAGE
- HIGH SHOCK SURVIVABILITY
- LEAD FREE AND ECOPACK COMPATIBLE

Description

The LIS3L02AS5 is a low-power three axcs linear accelerometer that includes a sensing element and an IC interface able to take the information from the sensing element and to provide an analog signal to the external world.

The sensing element, capable of catacting the acceleration, is manufactured using a dedicated process developed by ST to produce inertial sensors and actuators in silicon.

The IC interface is menuractured using a standard CMOS process that allows high level of integration



to design a dedicated circuit which is trimmed to better match the set sing element characteristics.

The LIS3L02AS5 has a user sole nuble full scale of $\pm 2\sigma$, $\pm 5\sigma$ and it is capable of measuring accelerations over a bondwidth of 1.5kHz for all axes. The device bandwidth may be reduced by using external capacitances. A self-test capability allows to check the mechanical and electrical signal nath of the sensor.

The LIS3L02AS5 is available in plastic SMD package and it is specified over an extended temperature range of -40° C to $+85^{\circ}$ C.

The LIS3L02AS5 belongs to a family of products suitable for a variety of applications:

- Mobile terminals
- Gaming and Virtual Reality input devices
- Free-fall detection for data protection
- Antitheft systems and Inertial Navigation
- Appliance and Robotics.

Order codes

Part number	Temp range, ° C	Package	Packing	
LIS3L02AS5	-40°C to +85°C	SO24	Tray	
LIS3L02AS5TR	-40°C to +85°C	SO24	Tape & Reel	

Contents

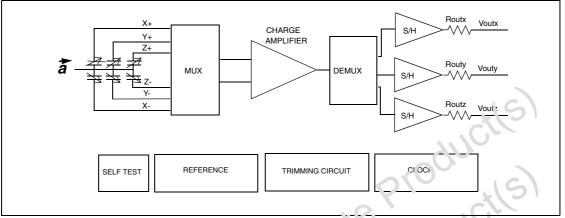
1	Bloc	k Diagram & Pins Description 3	;
	1.1	Block diagram	3
	1.2	Pin Description	}
2	Mech	anical and Electrical Specifications5	5
	2.1	Mechanical Characteristics 5	5
	2.2	Electrical Characteristics	3
	2.3	Absolute maximum ratings 7	7
	2.4	Terminology	,
3	Func	tionality)
	3.1	Sensing element)
	3.2	IC Interface)
	3.3	Factory calibration)
_		$O^{\vee} \times O^{\vee}$	_
4	Appli	ication hints	
	4.1	Soldering information	
	4.2	Output response vs orientation 11	
5	Pack	age Information	2
6	Revi.	aion history	;
Obs Obs		s Proor	
Obse			



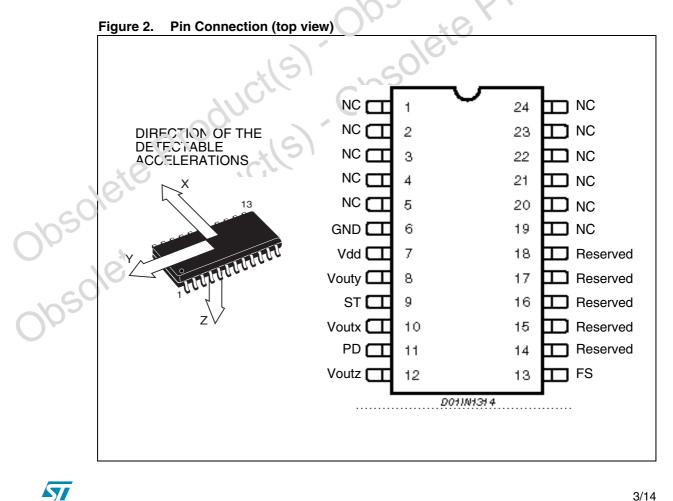
Block Diagram & Pins Description 1

Block diagram 1.1

Figure 1. **Block Diagram**



Pin Description 1.2



1 to 5	Pin # Pi	in Name	Function		
	1 to 5	NC	Internally not connected		
6	6	GND	0V supply		
7	7	Vdd	Power supply		
8	8	Vouty	Output Voltage		
9	9	ST	Self Test (Logic 0: normal mode; Logic 1: Self-test)		
10	10	Voutx	Output Voltage		
11	11	PD	Power Down (Logic 0: normal mode; Logic 1: Power-Down mode)		
12	12	Voutz	Output Voltage		
13	13	FS	Full Scale selection (Logic 0: 2g Full-scale; Logic 1: 6g Full-scale)		
14-15	14-15 R	eserved	Leave unconnected or connect to Vdd		
16	16 R	eserved	Connect to Vdd or ground		
17	17 R	eserved	Leave unconnected or connect to Vdd		
18	18 R	eserved	Leave unconnected or connect to ground		
19 to 24	19 to 24	NC	Internally not connected		
			(15) Obsolete Pro-		

Table 1. Pin description



2 Mechanical and Electrical Specifications

2.1 Mechanical Characteristics.

Table 2. Mechanical Characteristics¹

(Temperature range -40°C to +85°C) All the parameters specified @ Vdd = 5.0V, T = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ. ²	Max.	Unit
Ar	Assolutation Departa	FS pin connected to GND	±1.8	±2.0		g
AI	Acceleration Range ³	FS pin connected to Vdd	±5.4	±6.0	A	Sg
So	Sensitivity ⁴	Full-scale = 2g	Vdd/5-10%	Vdd/5	V1d/5	V/g
00	Sensitivity	Full-scale = 6g	Vdd/15-10%	Vdd/15	いきん 15+10%	V/g
SoDr	Sensitivity Change Vs Temperature	Delta from +25°C		±L J1	, ct	%/°C
Voff	Zero-g Level ⁴	T = 25°C	Vdd/2-10%	Vdd/2	Vdd/2+10%	V
OffDr	Zero-g level Change Vs Temperature	Delta from +25°C	SOL	±1.1	00	mg/°C
NL	Non Linearity ⁵	Best fit straight lir e Full-scale = 2g X, Y axis		e _{±0.3}	±1.5	% FS
		Best 1.t straight line; Fuli-scale = 2g Z axis	050	±0.6	±2	% FS
CrossAx	Cross-Axic	15		±2	±4	%
An	Acceleration Noise Density	Vdd=5.0V; Full-scale = 2g		50		µg/ √Hz
050	ote Prou	T = 25°C Vdd=5.0V Full-scale = 2g X axis	-70	-160	-320	mV
ovt O	Self test Output Voltage Change ^{7,8,9}	T = 25°C Vdd=5.0V Full-scale = 2g Y axis	70	160	320	mV
		T = 25°C Vdd=5.0V Full-scale = 2g Z axis	-70	-130	-320	mV
Fres	Sensing Element Resonance Frequency ¹⁰	all axes	1.5			KHz



Table 2. Mechanical Characteristics¹ (continued)

(Temperature range -40°C to +85°C) All the parameters specified @ Vdd = 5.0V, T = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ. ²	Max.	Unit
Тор	Operating Temperature Range		-40		+85	°C
Wh	Product Weight			0.6		gram

Note: 1 The product is factory calibrated at 5.0V. The device can be powered from 4.5V to 5.5V. Voff, So and Vt parameters will vary with supply voltage.

- 2 Typical specifications are not guaranteed
- 3 Verified by wafer level test and measurement of initial offset and sensitivity
- 4 Zero-g level and sensitivity are essentially ratiometric to supply voltage
- 5 Guaranteed by design
- 6 Contribution to the measuring output of an inclination/acceleration along any perpendicular axis
- 7 "Self test output voltage change" is defined as Vout(Vst=Logic1)-Vout(Vst=Logic0)
- 8 "Self test output voltage change" varies cubically with supply voltage
- 9 When full-scale is set to ±6g, "self-test output voltage change is one third of the specified value.
- 10 Minimum resonance frequency Fres=1.5KHz. Senser bandwidth=1/(2*π*110KΩ*Cload) with Cload>1nF.

2.2 Electrical Characteristics

Table 3. Electrical Characteristics¹

(Temperature range -4)°C to +85°C) All the parameters are specified @ Vdd =5.0V, T=25°C unless otherwise noted

P.t.P.

Symbol	Par a net er	Test Condition	Min.	Typ. ²	Max.	Unit
Vdd	Supply Voltage	R'	4.5	5	5.5	V
ldd	Supply Current	mean value PD pin connected to GND		1.0	1.5	mA
IdaPdn	Supply Current in Power Down Mode	rms value PD pin connected to Vdd		2.5	5	μA
Vst	Self Test Input	Logic 0 level	0		0.8	V
VSI		Logic 1 level	3.6		Vdd	V
Rout	Output Impedance		80	110	140	kΩ
Cload	Capacitive Load Drive ³		320			pF
Ton	Turn-On Time at exit from Power Down mode	Cload in μF		550*Cload+0.3		ms

Note: 1 The product is factory calibrated at 5.0V

2 Typical specifications are not guaranteed

3 Minimum resonance frequency Fres=1.5KHz. Sensor bandwidth=1/(2*π*110kΩ*Cload) with Cload>1nF



2.3 Absolute maximum ratings

Stresses above those listed as "absolute maximum ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device under these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Symbol	Ratings	Maximum Value	Unit
Vdd	Supply voltage	-0.3 to 7	V
Vin	Input Voltage on Any Control pin (FS, PD, ST)	-0.3 to Vdd +0.3	V
A _{POW}	Acceleration (Any axis, Powered, Vdd=5.0V)	3000g for 0.5 ms	6
APOM	Acceleration (Any axis, Fowered, Vdd=5.0V)	10000g for 0.1 ms	R
A _{UNP}	Acceleration (Any axis, Not powered)	3000g for 0.5 m3	
	Acceleration (Any axis, Not powered)	10000 j tor 0.1 ms	
T _{STG}	Storage Temperature Range	-40 to +125	°C
	1 Alexandree and a second s	2 (HBM)	kV
ESD	Electrostatic Discharge Protection	200 (MM)	V
	1050	1500 (CDM)	V

Table 4. Absolute maximum ratings



This is a Mechanical Shock pensitive device, improper handling can cause permanent damages to the part



This is an ESD sensitive device, improper handling can cause permanent damages to the part

2.4 Terminology

Sensitivity describes the gain of the sensor and can be determined by applying 1g occeleration to it. As the sensor can measure DC accelerations this can be done easily by pointing the axis of interest towards the center of the earth, note the output value, rotate the sensor by 180 degrees (point to the sky) and note the output value again thus applying $\pm 1g$ acceleration to the sensor. Subtracting the larger output value from the smaller one and dividing the result by 2 will give the actual sensitivity of the sensor. This value changes very little over temperature (see sensitivity change vs. temperature) and also very little over time. The Sensitivity Tolerance describes the range of Sensitivities of a large population of sensors.

Zero-g level describes the actual output signal if there is no acceleration present. A sensor in a steady state on an horizontal surface will measure 0g in X axis and 0g in Y axis whereas the Z axis will measure +1g. The output is ideally for a 5.0V powered sensor Vdd/2 = 2500mV. A deviation from ideal 0-g level (2500mV in this case) is called Zero-g offset. Offset of precise MEMS sensors is to some extend a result of stress to the sensor and therefore the offset can slightly change after mounting the sensor onto a printed circuit board or exposing it to extensive mechanical stress. Offset changes little over temperature - see "Zero-g Level Change vs. Temperature"- the Zero-g level of an individual sensor is very stable over lifetime. The Zero-g level tolerance describes the range of zero-g levels of a population of sensors.



Self Test allows to test the mechanical and electric part of the sensor, allowing the seismic mass to be moved by means of an electrostatic test-force. The Self Test function is off when the ST pin is connected to GND. When the ST pin is tied at Vdd an actuation force is applied to the sensor, simulating a definite input acceleration. In this case the sensor outputs will exhibit a voltage change in their DC levels which is related to the selected full scale and depending on the Supply Voltage through the device sensitivity. When ST is activated, the device output level is given by the algebraic sum of the signals produced by the acceleration acting on the sensor and by the electrostatic test-force. If the output signals change within the amplitude specified inside *Table 2*, than the sensor is working properly and the parameters of the interface chip are within the defined specification

Output impedance describes the resistor inside the output stage of each channel. This resistor is part of a filter consisting of an external capacitor of at least 320pF and the internal resistor. Due to the high resistor level only small, inexpensive external capacitors are needed to , into L unito L inition io generate low corner frequencies. When interfacing with an ADC it is important to use high input capacitance forms a corner frequency beyond the resonance frequency of the sensor. For a flat frequency response a corner frequency well below the resonance frequer cy is recommended. In general the smallest possible bandwidth for an particular application should be chosen to get



3 Functionality

The LIS3L02AS5 is a high performance, low-power, analog output three axes linear accelerometer packaged in a SO24 package. The complete device includes a sensing element and an IC interface able to take the information from the sensing element and to provide an analog signal to the external world.

3.1 Sensing element

A proprietary process is used to create a surface micro-machined accelerometer. The technology allows to carry out suspended silicon structures which are attached to the substrate in a few points called anchors and are free to move in the direction of the sensed acceleration. To be compatible with the traditional packaging techniques a cap is placed on top of the sensing element to avoid blocking the moving parts during the moulding place of the plastic encapsulation.

When an acceleration is applied to the sensor the proof mass displaces from its nominal position, causing an imbalance in the capacitive half-bridge. This imbalance is measured using charge integration in response to a voltage pulse applied in the sense capacitor.

At steady state the nominal value of the capacitors are tow pF and when an acceleration is applied the maximum variation of the capacitive load is up to 100fF.

3.2 IC Interface

In order to increase robustness and immunity against external disturbances the complete signal processing chain uses a fully differential structure. The final stage converts the differential signal into a single-orden one to be compatible with the external world.

The signals of the schedule element are multiplexed and fed into a low-noise capacitive charge amplifier that implements a Correlated Double Sampling (CDS) at its output to cancel the offset and the 1/1 noise. The output signal is de-multiplexed and transferred to three different S&Hs, one for each channel and made available to the outside.

Les low noise input amplifier operates at 200 kHz while the three S&Hs operate at a sampling frequency of 66 kHz. This allows a large oversampling ratio, which leads to in-band noise reduction and to an accurate output waveform.

All the analog parameters (zero-g level, sensitivity and self-test) are ratiometric to the supply voltage. Increasing or decreasing the supply voltage, the sensitivity and the offset will increase or decrease almost linearly. The self test voltage change varies cubically with the supply voltage.

3.3 Factory calibration

The IC interface is factory calibrated for Sensitivity (So) and Zero-g Level (Voff). The trimming values are stored inside the device by a non volatile structure. Any time the device is turned on, the trimming parameters are downloaded into the registers to be employed during the normal operation. This allows the user to employ the device without further calibration.



4 Application hints

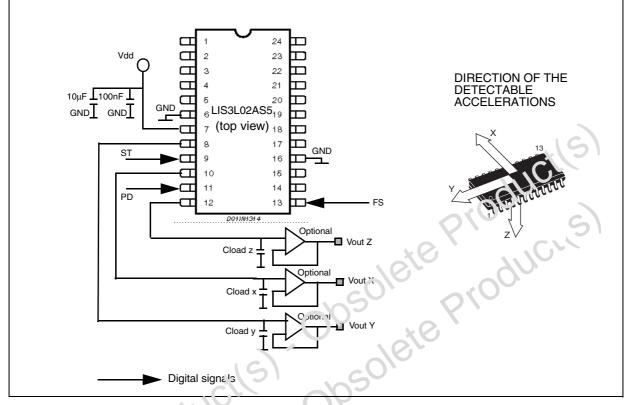


Figure 3. LIS3L02AS5 Electrical Connection

Power supply decoupling capacitors (100nF ceramic or polyester + 10µF Aluminum) should be placed as near as cossible to the device (common design practice).

The LIS3 02A35 allows to band limit Voutx, Vouty and Voutz through the use of external capacitors. The re-commended frequency range spans from DC up to 1.5 KHz. In particular, capacitors must be added at output pins to implement low-pass filtering for antialiasing and noise reduction. The equation for the cut-off frequency (f_t) of the external filters is:

$$f_{t} = \frac{1}{2\pi \cdot R_{out} \cdot C_{load}(x, y, z)}$$

Taking in account that the internal filtering resistor (R_{out}) has a nominal value equal to 110k Ω the equation for the external filter cut-off frequency may be simplified as follows:

$$f_{t} = \frac{1.45\mu F}{C_{load}(x, y, z)}[Hz]$$

The tolerance of the internal resistor can vary typically of $\pm 20\%$ within its nominal value of 110k Ω ; thus the cut-off frequency will vary accordingly. A minimum capacitance of 320pF for $C_{load}(x, y, z)$ is required in any case.



Capacitor value		
1500 nF		
150 nF		
68 nF		
30 nF		
15 nF		
6.8 nF		
3 nF		
-		

 Table 5.
 Filter Capacitor Selection, C_{load} (x,y,z).

4.1 Soldering information

The SO24 package is lead free qualified for soldering heat resistance according to JEDEC J-STD-020C.

4.2 Output response vs orientation

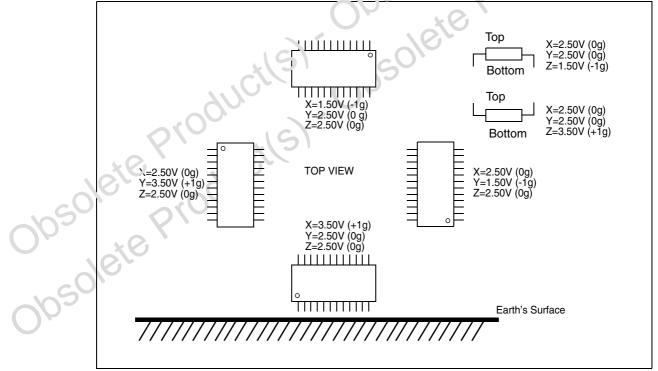


Figure 4. Output response vs orientation

Figure 4 refers to LIS3L02AS5 device powered at 5.0V

57

5 Package Information

In order to meet environmental requirements, ST offers these devices in ECOPACK[®] packages. These packages have a Lead-free second level interconnect. The category of second Level Interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label.

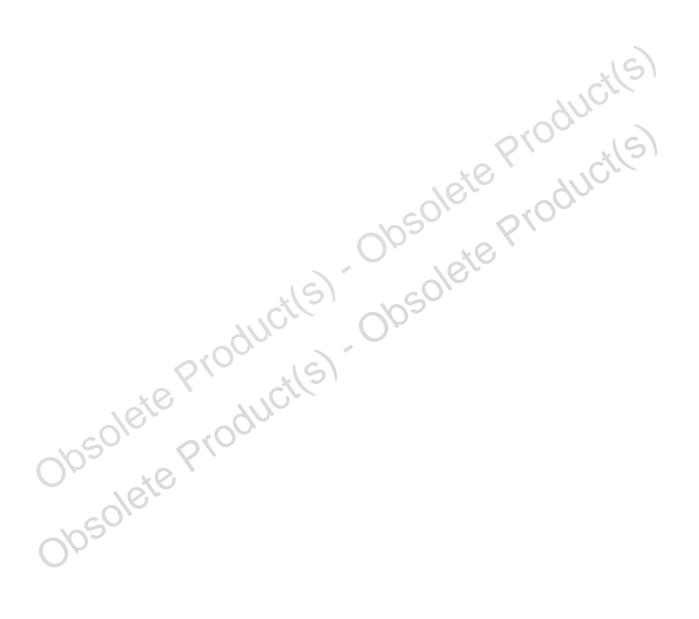
ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

mm inch DIM. **OUTLINE AND** МАХ. MIN. TYP. MAX. MIN. TYP. **MECHANICAL DATA** А 2.35 2.65 0.093 0.104 0.004 0.012 A1 0.10 0.30 0.200 в 0.33 0.51 0.013 Weight: 0.60g С 0.23 0.32 0.009 0.013 D ⁽¹⁾ 15.20 15.60 0.598 0.614 Е 7.40 7.60 0.291 0.299 е 1.27 0.050 0.394 н 10.0 10.65 0.419 0.25 h 0.75 0.010 0.030 L 0.40 1.27 0.016 0.050 k 0° (min.), 8° 'na '.) 0 004 ddd 0.10 SO24 (1) "D" dimension does not inc. tac. and flash, protusions or gate burrs. Mold flash, provisions or gate burrs shall not exceed 0.15mm per lic 3. D hx45* 1000 В A ddd С SEATING PIN 1 IDENTIFICATION PLANE С 0,25 mm GAGE PLANE m т A 0070769 C

Figure 5. SO24 Mechanical Data & Package Dimensions

6 Revision history

Date	Revision	Changes
1-Dec-2005	1	Initial release.





In formation furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics responsibility for the consequences authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

© 2005 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

